

- ☞ L1: (43066) MRAM or ((magnetoresistive or (magneto-resistive) or magnetic) near3 memory)
- ☞ L2: (20687) write near2 (line or conductor)
- ☞ L3: (6902) write adj2 driv\$4
- L4: (658) 1 same 2
- L5: (57) 3 same 4
- ☞ L6: (19988) disturb\$5 with (current or magnetic)
- ☞ L7: (3) 5 and 6
- L8: (582) (Hideaka near2 Hideto).in.
- L9: (47) 8 and 4
- ☞ L12: (897) 2 same 3
- ☞ L13: (13) 6 and 12
- ☞ L15: (578) 1 and 6
- L16: (30) 3 and 15
- ☞ L17: (1136) 365/158
- ☞ L18: (1251) 365/171
- L19: (878) 365/173
- L20: (215692) 365/
- ☞ L21: (52) 15 and 17
- ☞ L28: (66) 15 and 18
- ☞ L29: (26) 28 not 21
- L31: (63) 15 and 19
- L32: (15) 31 not (21 or 28)
- ☞ L33: (228) 15 and 20
- ☞ L34: (138) 33 not (21 or 28 or 31)
- L35: (37) (NAHAS near2 JOSEPH).in.
- L36: (87) (ANDRE near2 THOMAS).in.
- ☞ L37: (32) (SUBRAMANIAN near2 CHITRA).in
- ☞ L38: (16) 4 and 35
- L39: (14) 4 and 36
- L40: (13) 4 and 37
- L41: (431972) 257/
- ☞ L42: (50) 15 and 41
- ☞ L45: (92) 4 and 41
- L46: (89) 45 not 42
- L47: (440) 4 and 20
- ☞ L48: (406) 47 not 33

Search	Hit	Browse	Save	Open
DBs	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM; TL; <input checked="" type="checkbox"/> Biurels			
Default operator:		<input type="text" value="OR"/>		<input checked="" type="checkbox"/> Highlight all hit terms initially
<div> BRS term ISA R term Image Text HTML </div>				

U	1	2	Document IDv	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cla	Inventor	S	C	P	A
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6661071 B2	20031209	7	Memory having plural magnetic layers and a shielding layer	257/422	257/414; 257/421		Leusssen, Kars-Michiël Lubart et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6611454 B2	20030826	36	Thin film magnetic memory device writing data of a plurality of bits in	365/171	365/189.04; 365/190		Hidaka, Hideto	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6577527 B2	20030610	7	Method for preventing unwanted programming in an MRAM consisting	365/158	365/209		Freitag, Martin et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	
4	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040001353 A1	20040101	53	Thin film magnetic memory device suppressing internal magnetic noise	365/171			Hidaka, Hideto	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	
5	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20030174536 A1	20030918	29	Thin film magnetic memory device applying a magnetic field to write	365/158			Hidaka, Hideto	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	
6	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020135018 A1	20020926	37	THIN FILM MAGNETIC MEMORY	257/359			Hidaka, Hideto	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	